imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

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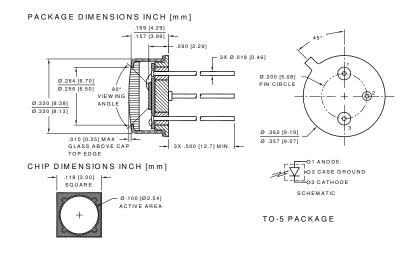




UV Enhanced Silicon Photodiode SD100-13-23-222

Precision – Control – Results





DESCRIPTION

The **SD 100-13-23-222** is UV enhanced silicon PIN photodiode assembled in a hermetic TO-5 metal package with isolated pins.

This API high-reliability detector is in principle able to meet military test

requirements (Mil-STD-750, Mil-STD-883) after proper screening and group test.

FEATURES

- Low Noise
- High Speed
- High shunt resistance
- High response

APPLICATIONS

- Instrumentation
- Medical
- Industrial

Contact API for recommendations on specific test conditions and procedures.

RELIABILITY

ABSOLUTE MAXIMUM RATINGS

MIN	MAX	UNITS	$T_a = 23^{\circ}C$				
-	50	V	non condensing				
-40	+125	°C					
-55	+150	°C					
-	+260	°C	see recommended reflow profile				
	-40	- 50 -40 +125 -55 +150	- 50 V -40 +125 °C -55 +150 °C				

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UV Enhanced Silicon Photodiode SD100-13-23-222

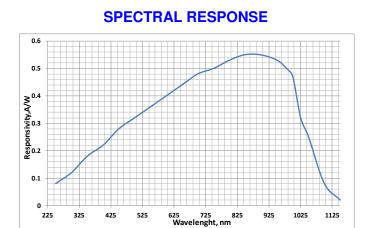
Precision – Control – Results

OPTO-ELECTRICAL PARAMETERS

 $T_a = 23^{\circ}C$ unless noted otherwise

CHARACTERISTIC	TEST CONDITIONS	MIN	ТҮР	MAX	UNITS
Dark Current	$V_{\rm R} = 5V$	-	1	6.5	nA
Shunt Resistance	$V_{\rm R} = 10 \text{ mV}$	200	300	-	MΩ
Junction Capacitance	$V_{R} = 0 V$, $f = 1 MHz$	-	90	-	pF
Junction Capacitance	$V_{\rm R} = 50 \text{ V}, \text{ f} = 1 \text{ MHz}$	-	9	-	pF
Spectral Application Range	Spot Scan	250	-	1100	nm
Responsivity	I= 365 nm V, V _R = 0 V	0.10	0.18	-	A/W
Breakdown Voltage	I = 10 μA	30	50	-	V
Noise Equivalent Power	V _R = 0V @ I=Peak	-	3x10 ⁻¹⁴	-	$W/Hz^{1/2}$
Response Time	$RL = 50 \ \Omega, V_R = 0 \ V$	-	190	-	nS
	RL = 50 Ω, V _R = 10 V	-	13	-	
	TYDICAL	DEDEODMA	NOE		

TYPICAL PERFORMANCE



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